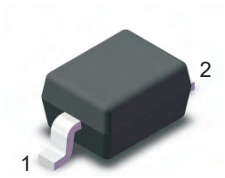
BAV19WS~BAV21WS
Silicon Epitaxial Planar Switching Diode

Features

- For surface mount applications
- Glass passivated chip junction
- Low profile package
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directive

SOD-323



1.Cathode — 2.Anode

Marking Code:

BAV19WS: A8
BAV20WS: T2
BAV21WS: T3

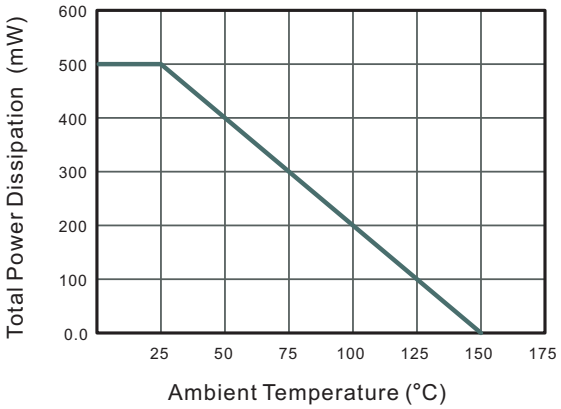
Absolute Maximum Ratings at T_A = 25 ℃

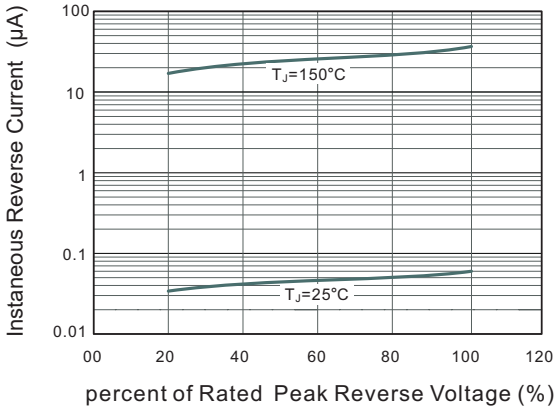
Parameter		Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	BAV19WS	V_{RRM}	120	V
	BAV20WS		200	
	BAV21WS		250	
Maximum RMS Voltage	BAV19WS	V_{RMS}	100	V
	BAV20WS		150	
	BAV21WS		200	
Continuous Forward Current		I_F	250	mA
Repetitive Peak Forward Current		I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	at t =1 s	I_{FSM}	1	A
	at t =1 ms		3	
	at t =1 μs		9	
Power Dissipation		P_D	500	mW
Junction Temperature		T_J	500	°C
Storage Temperature Range		T_{STG}	-55 to +150	°C

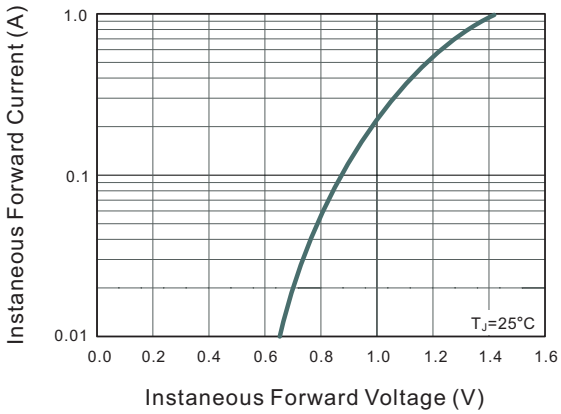
Characteristics at T_A = 25 ℃

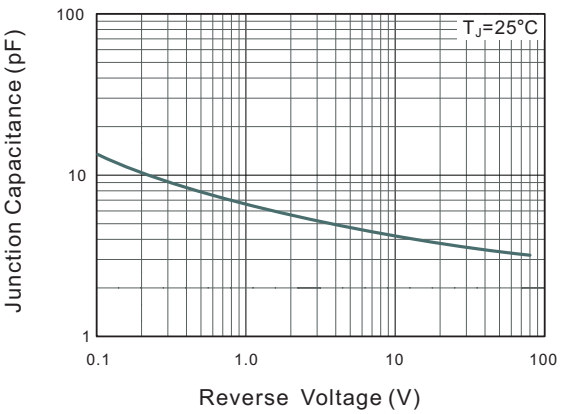
Parameter		Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 100 μA	BAV19WS BAV20WS BAV21WS	$V_{(BR)R}$	120 200 250	-- -- --	V
Maximum Forward Voltage at I_F =100 mA at I_F =200 mA		V_F	-- --	1 1.25	V
Maximum DC Reverse Current at Rated DC Blocking Voltage at T_A =25 °C at T_A =150 °C		I_R	-- --	0.1 100	μA
Typical Junction Capacitance at V_R= 4 V, f= 1 MHz		C_j	--	5	pF
Maximum Reverse Recovery Time at I_F= 0.5 A, I_{rr}= 0.25A, I_R= 1A		T_{rr}	--	50	nS

Typical Characteristic Curves





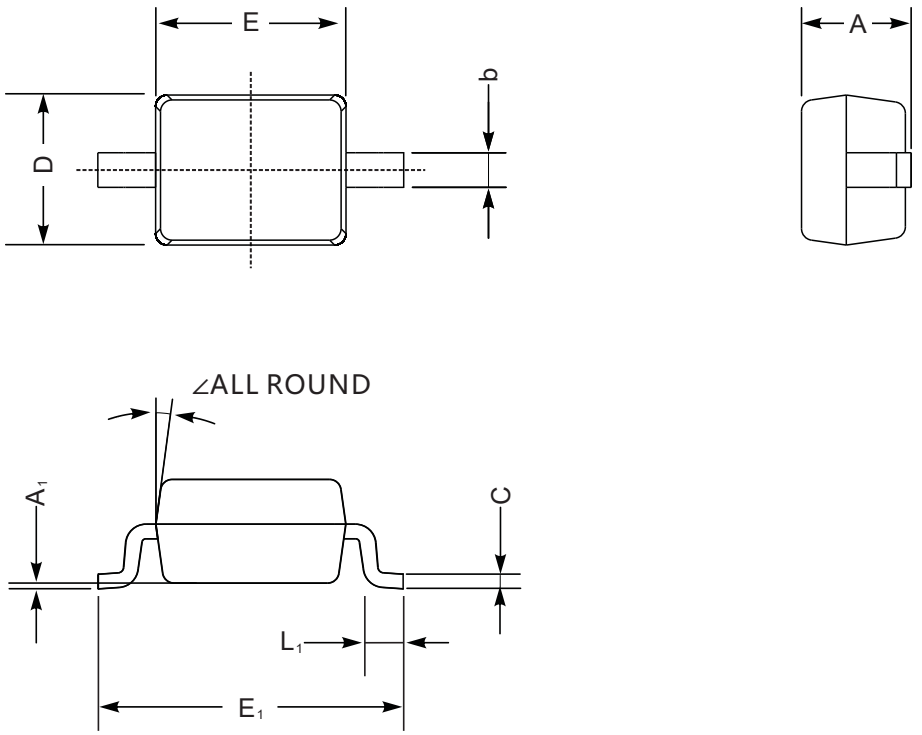




Package Outline

SOD-323

Dimensions in mm



UNIT		A	C	D	E	E_1	b	L_1	A_1	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	